

# NTS4409N

## Small Signal MOSFET

25 V, 0.75 A, Single, N-Channel,  
ESD Protection, SC-70/SOT-323

### Features

- Advance Planar Technology for Fast Switching, Low  $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- This is a Pb-Free Device

### Applications

- Boost and Buck Converter
- Load Switch
- Battery Protection

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	25	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 8.0$	V	
Drain Current	$t < 5 \text{ s}$ $T_A = 25^\circ\text{C}$	$I_D$	0.75	A	
Continuous Drain Current (Note 1)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	0.7	A
			$T_A = 75^\circ\text{C}$	0.6	
Power Dissipation (Note 1)	Steady State	$P_D$	0.28	W	
Power Dissipation (Note 1)	$t \leq 5 \text{ s}$	$P_D$	0.33	W	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	3.0	A	
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$	
Source Current (Body Diode) (Note 1)		$I_S$	0.3	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	
ESD Rating - Machine Model			250	V	

### THERMAL RESISTANCE RATINGS

Rating	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	450	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 5 \text{ s}$ (Note 1)	$R_{\theta JA}$	375	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

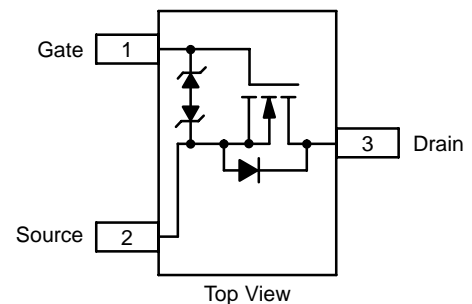


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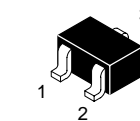
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
25 V	249 m $\Omega$ @ 4.5 V	0.75 A
	299 m $\Omega$ @ 2.7 V	

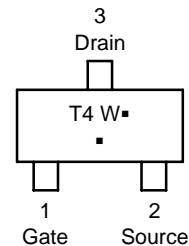
### SC-70 (3-Leads)



### MARKING DIAGRAM & PIN ASSIGNMENT



SC-70/SOT-323  
CASE 419  
STYLE 8



T4 = Device Code  
W = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTS4409NT1G	SOT-323 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			30		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$	$T_J = 25^\circ\text{C}$		0.5	$\mu\text{A}$
			$T_J = 70^\circ\text{C}$		2.0	
			$T_J = 125^\circ\text{C}$		5.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 8.0\text{ V}$			100	nA

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	0.65		1.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-2.0		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 0.6\text{ A}$		249	350	m $\Omega$
		$V_{GS} = 2.7\text{ V}, I_D = 0.2\text{ A}$		299	400	
		$V_{GS} = 4.5\text{ V}, I_D = 1.2\text{ A}$		260		
Forward Transconductance	$g_{FS}$	$V_{DS} = 5.0\text{ V}, I_D = 0.5\text{ A}$		0.5		S

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 10\text{ V}$		49	60	pF
Output Capacitance	$C_{OSS}$			22.4	30	
Reverse Transfer Capacitance	$C_{RSS}$			8.0	12	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 0.8\text{ A}$		1.2	1.5	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	$Q_{GS}$			0.28	0.50	
Gate-to-Drain Charge	$Q_{GD}$			0.3	0.40	

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 0.7\text{ A}, R_G = 51\ \Omega$		5.0	12	ns
Rise Time	$t_r$			8.2	8.0	
Turn-Off Delay Time	$t_{d(OFF)}$			23	35	
Fall Time	$t_f$			41	60	

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 0.6\text{ A}$	$T_J = 25^\circ\text{C}$		0.82	1.20	V
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- Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

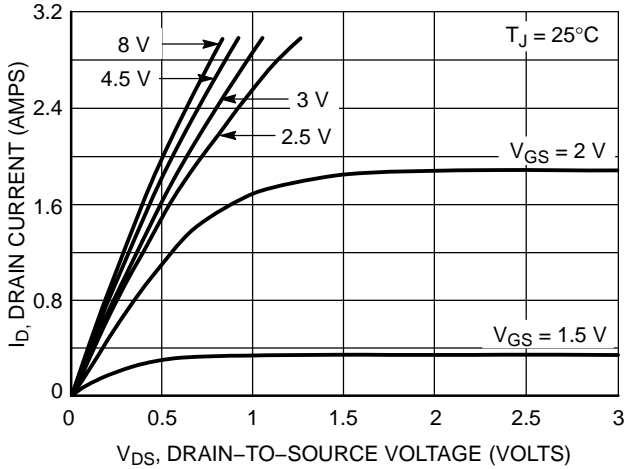


Figure 1. On-Region Characteristics

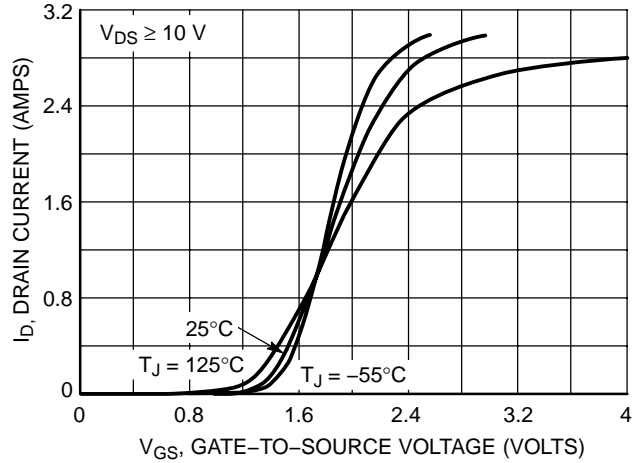


Figure 2. Transfer Characteristics

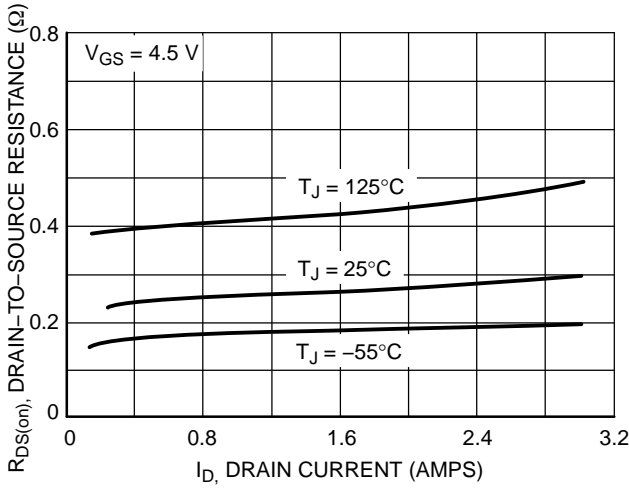


Figure 3. On-Resistance vs. Drain Current and Temperature

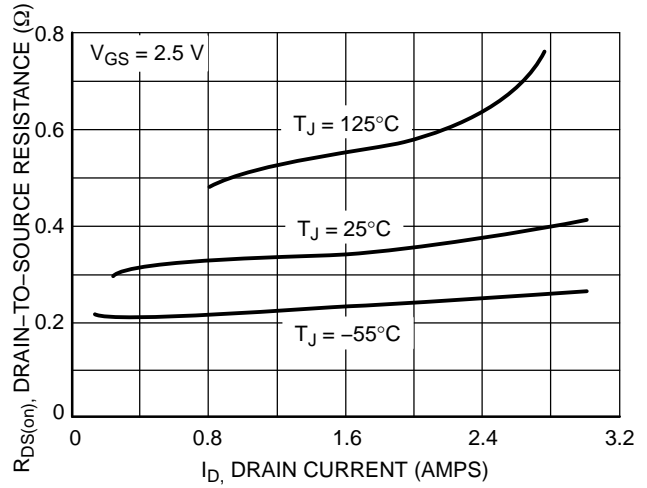


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

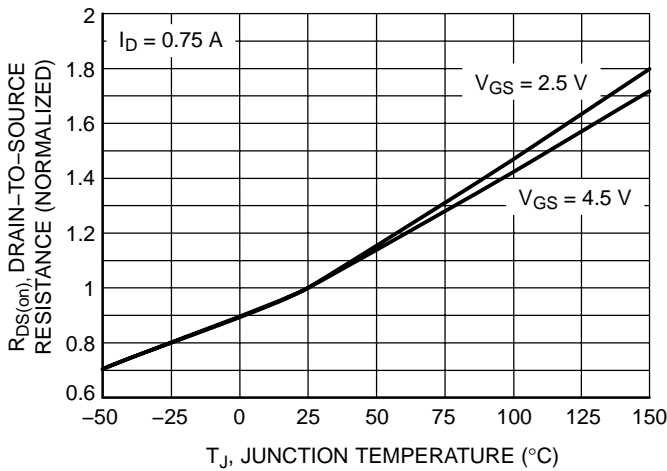


Figure 5. On-Resistance Variation with Temperature

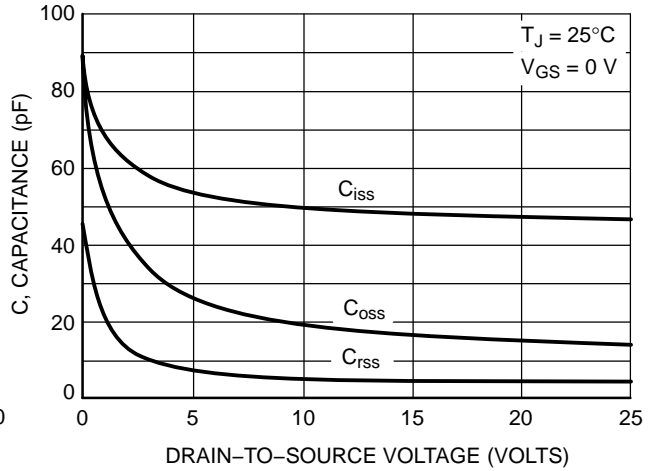
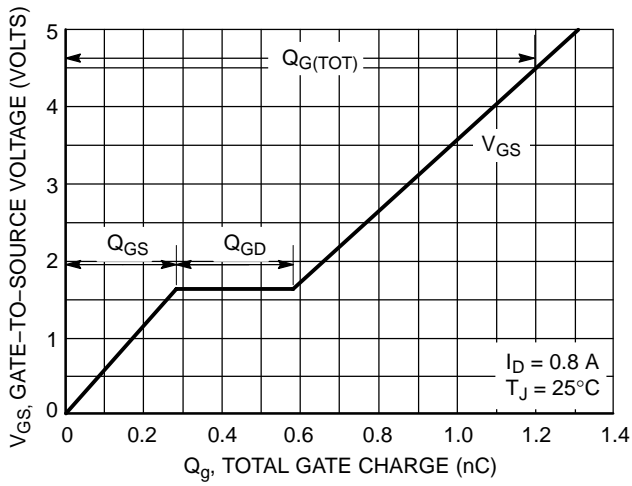


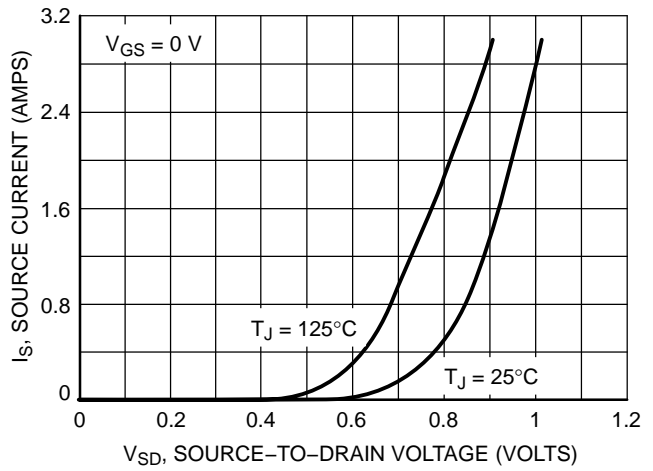
Figure 6. Capacitance Variation

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



**Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge**

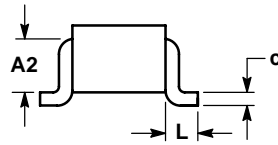
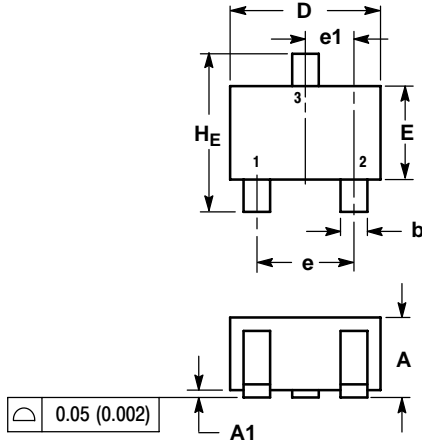


**Figure 8. Diode Forward Voltage vs. Current**

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## PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE M

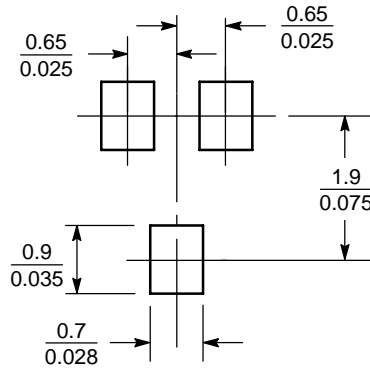


NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 8:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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